









SN65C3232, SN75C3232 SLLS540C - JULY 2002 - REVISED JUNE 2021

3-V to 5.5-V Multichannel RS-232 Compatible Line Driver and Receiver

1 Features

- Operate with 3-V to 5.5-V V_{CC} supply
- Operate up to 1 Mbit/s
- Low supply current: 300 µA typical
- External capacitors: 4 × 0.1 µF
- Accept 5-V logic input with 3.3-V supply
- RS-232 bus-pin ESD protection exceeds ±15 kV using human-body model (HBM)

2 Applications

- **Industrial PCs**
- Wired networking
- Data center and enterprise computing
- Battery-powered systems
- Notebooks
- Laptops
- Palmtop PCs
- Hand-held equipment

3 Description

The SN65C3232 and SN75C3232 consist of two line drivers, two line receivers, and a dual chargepump circuit with ±15-kV ESD protection pin-to-pin (serial-port connection pins, including GND). These devices provide the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at typical data signaling rates up to 1 Mbit/s and a driver output slew rate of 24 V/µs to 150 V/µs.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)
SN65C3232 SN75C3232	D (SOIC) (16)	9.90 mm x 3.91 mm
	DB (SSOP) (16)	6.20 mm x 5.30 mm
	DW (SOIC) (16)	10.3 mm x 7.50 mm
	PW (TSSOP) (16)	5.00 mm v 4.40 mm

For all available packages, see the orderable addendum at the end of the data sheet.

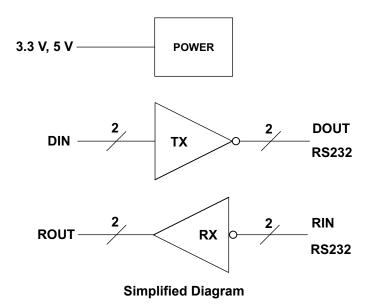




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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (November 2004) to Revision C (June 2021)

Page

- Added Applications: Industrial PCs, Wired networking, and Data center and enterprise computing......1

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5 Pin Configuration and Functions

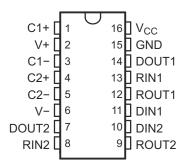


Figure 5-1. D, DW, DB and PW Package, 16-Pin SOIC, SSOP and TSSOP, Top View

PIN		1/0	DESCRIPTION	
NAME	NO.	I/O	DESCRIPTION	
C1+	1	_	Positive lead of C1 capacitor	
V+	2	0	ositive charge pump output for storage capacitor only	
C1-	3	_	Negative lead of C1 capacitor	
C2+	4	_	Positive lead of C2 capacitor	
C2-	5	_	Negative lead of C2 capacitor	
V-	6	0	Negative charge pump output for storage capacitor only	
DOUT2	7	0	RS232 line data output (to remote RS232 system)	
RIN2	8	I	RS232 line data input (from remote RS232 system)	
ROUT2	9	0	Logic data output (to UART)	
DIN2	10	I	Logic data input (from UART)	
DIN1	11	I	Logic data input (from UART)	
ROUT1	12	0	Logic data output (to UART)	
RIN1	13	I	RS232 line data input (from remote RS232 system)	
DOUT1	14	0	RS232 line data output (to remote RS232 system)	
GND	15	_	Ground	
V _{CC}	16	_	Supply Voltage, Connect to external 3-V to 5.5-V power supply	



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range ⁽²⁾		-0.3	6	V
V+	Positive-output supply voltage ra	Positive-output supply voltage range ⁽²⁾		7	V
V-	Negative-output supply voltage range ⁽²⁾		0.3	-7	V
V+ – V–	Supply voltage difference ⁽²⁾			13	V
V	land to alter a new an	Drivers	-0.3	6	V
V _I	Input voltage range	Receivers	-25	25	V
V	Output voltage range	Drivers	-13.2	13.2	V
Vo	Output voltage range	Receivers	-0.3	V _{CC} + 0.3	V
TJ	Operating virtual junction temper	ature		150	°C
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute MaximumRatings do not imply functional operation of the device at these or any other conditions beyond those listed underRecommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

6.2 ESD Ratings

				VALUE	UNIT
V _(ESD) Electrost		Human body model (HBM), per ANSI/	All pins except RIN and DOUT	±3000	
	Electrostatic discharge	ESDA/JEDEC JS-001 ⁽¹⁾	RIN and DOUT Pins	±15,000	V
(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	All pins	±1500	

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

See Typical Operating Circuit and Capacitor Values, See (1)

			MIN	NOM	MAX	UNIT
Cumply valtage		V _{CC} = 3.3 V	3	3.3	3.6	V
Supply voltage		V _{CC} = 5 V	4.5	5	5.5	V
Driver high-level input voltage	DIN	V _{CC} = 3.3 V	2			V
	DIN	V _{CC} = 5 V	2.4			V
Driver low-level input voltage	DIN				0.8	V
Driver input voltage	DIN		0		5.5	V
Receiver input voltage			-25		25	V
		SN75C3232	0		70	°C
Operating free-air temperature		SN65C3232	-40		85	, C
	Driver input voltage Driver input voltage	Driver high-level input voltage DIN Driver low-level input voltage DIN Driver input voltage DIN Receiver input voltage	Supply voltage	Supply voltage	Supply voltage $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Supply voltage $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V.

⁽²⁾ All voltages are with respect to network GND.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.4 Thermal Information

	THERMAL METRIC(1)	PW (TSSOP)	D (SOIC)	DW (SOIC)	DB (SSOP)	UNIT
		16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	108.0	85.9	57.0	46.0	°C/W
R _{θJCtop}	Junction-to-case (top) thermal resistance	20.8	43.1	33.5	36.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	45.1	44.5	37.1	43.8	°C/W
ΨЈТ	Junction-to-top characterization parameter	0.6	10.1	7.5	4.2	°C/W
ΨЈВ	Junction-to-board characterization parameter	45.1	44.1	37.1	42.9	°C/W
R _{0JCbot}	Junction-to-case (bottom) thermal resistance	_	_	_	_	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Typical Operating Circuit and Capacitor Values)

	PARAMETER ⁽²⁾	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
I_{CC}	Supply current	No load, V _{CC} = 3.3 V or 5 V		0.3	1	mA

⁽¹⁾ All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

⁽²⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.



6.6 Driver Section - Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Typical Operating Circuit and Capacitor Values)

PARAMETER		TEST CONDITIONS(3)		MIN	TYP ⁽¹⁾	MAX	UNIT
V _{OH}	High-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	DIN = GND	5	5.4		V
V _{OL}	Low-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	DIN = V _{CC}	-5	-5.4		V
I _{IH}	High-level input current	V _I = V _{CC}	V _I = V _{CC}		±0.01	±1	μA
I _{IL}	Low-level input current	V _I at GND			±0.01	±1	μΑ
	Short-circuit output current ⁽²⁾	V _O = 0 V	V _{CC} = 3.6 V		±35	±60	mΛ
los	Short-circuit output current	V _O = 0 V	V _{CC} = 5.5 V		±35	±1	mA
r _o	Output resistance	V _{CC} , V+, and V– = 0 V,	V _O = ±2 V	300	10M		Ω

- (1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
- (2) Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.
- (3) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V.

6.7 Switching Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Typical Operating Circuit and Capacitor Values)

	PARAMETER		TEST CONDITIONS(3)		MIN	TYP ⁽¹⁾ MA	UNIT
			C _L = 1000 pF		250		
	Maximum data rate (see Figure 7-1)	$R_L = 3 \text{ k}\Omega$, One DOUT switching	C _L = 250 pF,	V_{CC} = 3 V to 4.5 V	1000		kbit/s
	(See Figure 7-1)		C _L = 1000 pF,	V _{CC} = 4.5 V to 5.5 V	1000		
t _{sk(p)}	Pulse skew ⁽²⁾	C _L = 150 pF to 2500 pF,	R_L = 3 kΩ to 7 kΩ,	See Figure 7-2		300	ns
SR(tr)	Slew rate, transition region (see Figure 7-1)	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$	C _L = 150 pF to 1000 pF,	V _{CC} = 3.3 V	18	15	V/µs

- (1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
- (2) Pulse skew is defined as $|t_{PLH} t_{PHL}|$ of each channel of the same device.
- (3) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.



6.8 Receiver Section - Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Typical **Operating Circuit and Capacitor Values)**

	PARAMETER	TEST CONDITIONS(2)	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{OH}	High-level output voltage	I _{OH} = -1 mA	V _{CC} - 0.6	V _{CC} - 0.1		V
V _{OL}	Low-level output voltage	I _{OL} = 1.6 mA		-	0.4	V
V _{IT+}	Positive-going input threshold voltage	V _{CC} = 3.3 V		1.5	2.4	V
		V _{CC} = 5 V		1.8	2.4	V
\/	Negative going input threshold voltage	V _{CC} = 3.3 V	0.6	1.2		V
V_{IT-}	Negative-going input threshold voltage	V _{CC} = 5 V	0.8	1.5		V
V _{hys}	Input hysteresis (V _{IT+} - V _{IT-})			0.3		V
r _i	Input resistance	V _I = ±3 V to ±25 V	3	5	7	kΩ

⁽¹⁾

6.9 Switching Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Typical **Operating Circuit and Capacitor Values)**

	PARAMETER	TEST CONDITIONS(3)	TYP ⁽¹⁾	UNIT
t _{PLH}	Propagation delay time, low- to high-level output	C _L = 150 pF	300	ns
t _{PHL}	Propagation delay time, high- to low-level output	C _L = 150 pF	300	ns
t _{sk(p)}	Pulse skew ⁽²⁾		300	ns

All typical values are at V $_{CC}$ = 3.3 V or V $_{CC}$ = 5 V, and T $_{A}$ = 25°C. Test conditions are C1–C4 = 0.1 μ F at V $_{CC}$ = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V $_{CC}$ = 5 V \pm 0.5 V.

⁽¹⁾ All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C. (2) Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device. (3) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V.



6.10 Typical Characteristics

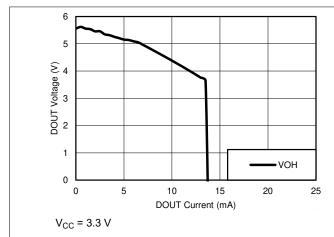


Figure 6-1. DOUT V_{OH} vs Load Current, Both Drivers Loaded

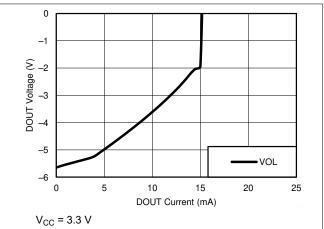
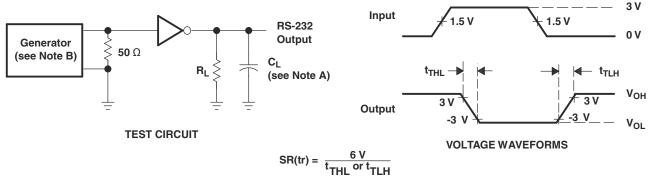


Figure 6-2. DOUT V_{OL} vs Load Current, Both Drivers Loaded

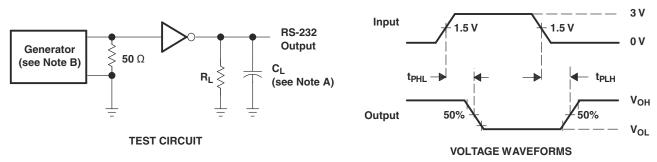


7 Parameter Measurement Information



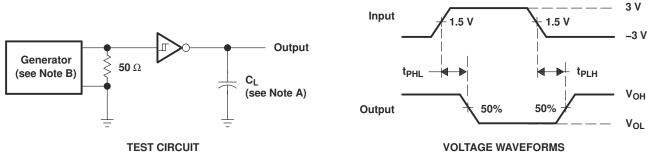
- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_0 = 50 Ω , 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 7-1. Driver Slew Rate



- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_0 = 50 \Omega$, 50% duty cycle, $t_r \le 10$ ns.

Figure 7-2. Driver Pulse Skew



- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: Z_0 = 50 Ω , 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 7-3. Receiver Propagation Delay Times

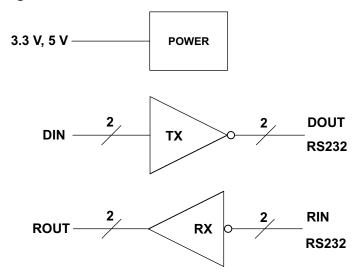


8 Detailed Description

8.1 Overview

The devices consists of two line drivers, two-line receivers, and a dual charge-pump circuit with IEC61000-4-2 ESD protection terminal to terminal (serial-port connection terminals, including GND). The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The device operates at data signaling rates up to 250 kbit/s and a maximum of 30-V/µs driver output slew rate. Outputs are protected against shorts to ground.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Power

The power block increases, inverts, and regulates voltage at V+ and V- pins using a charge pump that requires four external capacitors.

8.3.2 RS232 Driver

Two drivers interface standard logic level to RS232 levels. Both DIN inputs must be valid high or low.

8.3.3 RS232 Receiver

Two receivers interface RS232 levels to standard logic levels. An open input will result in a high output on ROUT. Each RIN input includes an internal standard RS232 load.



8.4 Device Functional Modes

Table 8-1 and Table 8-2 list the functional modes of the drivers and receivers of MAX3232E.

Table 8-1. Each Driver⁽¹⁾

	OUTPUT DOUT
L	Н
Н	L

(1) H = high level, L = low level

Table 8-2. Each Receiver(1)

	OUTPUT ROUT
L	Н
Н	L
Open	Н

(1) H = high level, L = low level,Open = input disconnected or connected driver off

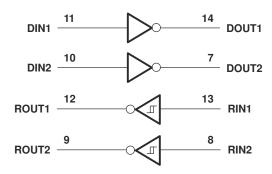


Figure 8-1. Logic Diagram

8.4.1 V_{CC} Powered by 3 V to 5.5 V

The device is in normal operation.

8.4.2 V_{CC} Unpowered, $V_{CC} = 0 V$

When the device is unpowered, it can be safely connected to an active remote RS232 device.

9 Application and Implementation

Note

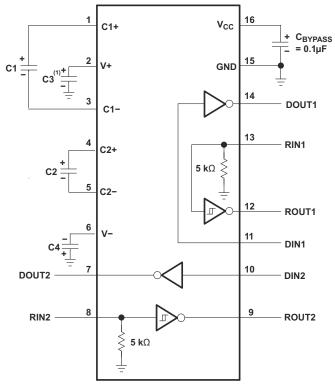
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

For proper operation, add capacitors as shown in Table 9-1.

9.1.1 Typical Application

ROUT and DIN connect to UART or general-purpose logic lines. RIN and DOUT lines connect to a RS232 connector or cable.



- A. C3 can be connected to V_{CC} or GND
 - A. Resistor values shown are nominal.
 - B. Nonpolorized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

Figure 9-1. Typical Operating Circuit and Capacitor Values

 V_{CC}
 C1
 C2, C3, C4

 3.3 V ± 0.3 V
 0.1 μF
 0.1 μF

 5 V ± 0.5 V
 0.047 μF
 0.33 μF

 3 V to 5.5 V
 0.1 μF
 0.47 μF

Table 9-1. VCC vs Capacitor Values



9.1.1.1 Design Requirements

The recommended V_{CC} is 3.3 V or 5 V. 3 V to 5.5 V is also possible

The maximum recommended bit rate is 250 kbit/s.

9.1.1.2 Detailed Design Procedure

All DIN inputs must be connected to valid low or high logic levels.

Select capacitor values based on V_{CC} level for best performance.

9.1.1.3 Application Performance Plots

Figure 9-2 curves are for 3.3-V VCC and 250-kbit/s alternative bit data stream.

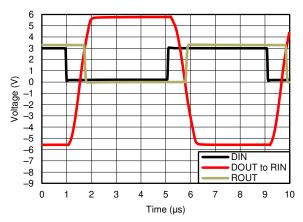


Figure 9-2. 250 kbit/s Driver to Receiver Loopback Timing Waveform, V_{CC} = 3.3 V



10 Layout

10.1 Layout Guidelines

Keep the external capacitor traces short, specifically on the C1 and C2 nodes that have the fastest rise and fall times.

10.2 Layout Example

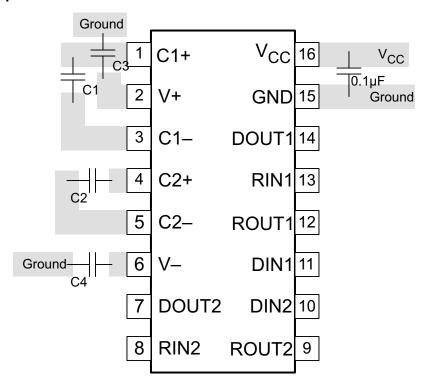


Figure 10-1. Layout Diagram



11 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

11.1 Documentation Support

11.1.1 Related Documentation

11.1.1.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to order now.

11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

11.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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11.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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23-May-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking
	. ,	. ,			. ,	(4)	(5)		. ,
SN65C3232D	Obsolete	Production	SOIC (D) 16		-	Call TI	Call TI	-40 to 85	65C3232
SN65C3232DBR	Active	Production	SSOP (DB) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232
SN65C3232DBR.A	Active	Production	SSOP (DB) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232
SN65C3232DR	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232
SN65C3232DR.A	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232
SN65C3232DRG4.A	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232
SN65C3232DW	Active	Production	SOIC (DW) 16	40 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232
SN65C3232DW.A	Active	Production	SOIC (DW) 16	40 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232
SN65C3232DWR	Active	Production	SOIC (DW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232
SN65C3232DWR.A	Active	Production	SOIC (DW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232
SN65C3232PWR	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3232
SN65C3232PWR.A	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3232
SN75C3232D	Obsolete	Production	SOIC (D) 16	-	-	Call TI	Call TI	0 to 70	75C3232
SN75C3232DBR	Active	Production	SSOP (DB) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3232
SN75C3232DBR.A	Active	Production	SSOP (DB) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	CA3232
SN75C3232DR	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3232
SN75C3232DR.A	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3232
SN75C3232DW	Active	Production	SOIC (DW) 16	40 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3232
SN75C3232DW.A	Active	Production	SOIC (DW) 16	40 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3232
SN75C3232DWR	Active	Production	SOIC (DW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3232
SN75C3232DWR.A	Active	Production	SOIC (DW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3232

⁽¹⁾ Status: For more details on status, see our product life cycle.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.



PACKAGE OPTION ADDENDUM

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(4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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TAPE AND REEL INFORMATION



TAPE DIMENSIONS WHO WE PI WHO WE PI WHO WE BO WE Cavity A O WE Cavity

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3232DBR	SSOP	DB	16	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN65C3232DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN65C3232DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
SN65C3232PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN65C3232PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN75C3232DBR	SSOP	DB	16	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN75C3232DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN75C3232DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1



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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3232DBR	SSOP	DB	16	2000	356.0	356.0	35.0
SN65C3232DR	SOIC	D	16	2500	356.0	356.0	35.0
SN65C3232DWR	SOIC	DW	16	2000	350.0	350.0	43.0
SN65C3232PWR	TSSOP	PW	16	2000	356.0	356.0	35.0
SN65C3232PWR	TSSOP	PW	16	2000	356.0	356.0	35.0
SN75C3232DBR	SSOP	DB	16	2000	356.0	356.0	35.0
SN75C3232DR	SOIC	D	16	2500	356.0	356.0	35.0
SN75C3232DWR	SOIC	DW	16	2000	350.0	350.0	43.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN65C3232DW	DW	SOIC	16	40	506.98	12.7	4826	6.6
SN65C3232DW.A	DW	SOIC	16	40	506.98	12.7	4826	6.6
SN75C3232DW	DW	SOIC	16	40	506.98	12.7	4826	6.6
SN75C3232DW.A	DW	SOIC	16	40	506.98	12.7	4826	6.6

D (R-PDS0-G16)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-150.





NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



7.5 x 10.3, 1.27 mm pitch

SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing
- per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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